STGW40NC60V

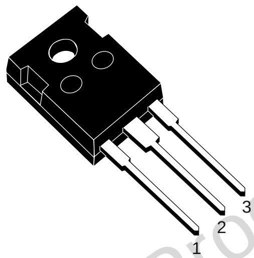
N-CHANNEL 50A - 600V - TO-247
Very Fast PowerMESH™ IGBT

Table 1: General Features

TYPE	V_{CES}	$V_{CE(sat)}$ (Max) @25°C	I_C @100°C
STGW40NC60V	600 V	< 2.5 V	50 A

- HIGH CURRENT CAPABILITY
- HIGH FREQUENCY OPERATION UP TO 50 KHz
- LOSSES INCLUDE DIODE RECOVERY ENERGY
- OFF LOSSES INCLUDE TAIL CURRENT
- LOWER C_{RES} / C_{IES} RATIO
- NEW GENERATION PRODUCTS WITH TIGHTER PARAMETER DISTRUBUTION

Figure 1: Package



TO-247

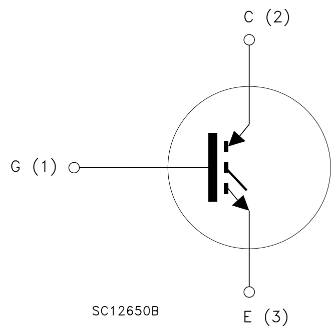
Weight: 4.41gr ± 0.01

Max Clip Pressure: 150 N/mm^2

DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "V" identifies a family optimized for high frequency.

Figure 2: Internal Schematic Diagram



APPLICATIONS

- HIGH FREQUENCY INVERTERS
- SMPS and PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES
- UPS
- MOTOR DRIVERS

Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGW40NC60V	GW40NC60V	TO-247	TUBE

Rev. 10

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value	Symbol
V_{CES}	Collector-Emitter Voltage (V_{GS} = 0)	600	V
V_{ECR}	Reverse Battery Protection	20	V
V_{GE}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current (continuous) at 25°C (#)	80	A
I_C	Collector Current (continuous) at 100°C (#)	50	A
I_{CM} (1)	Collector Current (pulsed)	200	A
P_{TOT}	Total Dissipation at T_C = 25°C	260	W
	Derating Factor	2.08	W/°C
T_{stg}	Storage Temperature	– 55 to 150	°C
T_j	Operating Junction Temperature		

(1)Pulse width limited by max. junction temperature.

Table 4: Thermal Data

		Min.	Typ.	Max.	Unit
Rthj-case	Thermal Resistance Junction-case			0.48	°C/W
Rthj-amb	Thermal Resistance Junction-ambient			50	°C/W
T_L	Maximum Lead Temperature for Soldering Purpose (1.6 mm from case, for 10 sec.)		300		°C

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

Table 5: Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collectro-Emitter Breakdown Voltage	I_C = 1 mA, V_{GE} = 0	600			V
I_{CES}	Collector-Emitter Leakage Current (V_{CE} = 0)	V_{GE} = Max Rating Tc=25°C Tc=125°C			 10 1	 µA mA
I_{GES}	Gate-Emitter Leakage Current (V_{CE} = 0)	V_{GE} = ± 20 V , V_{CE} = 0			± 100	nA

Table 6: On

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Threshold Voltage	V_{CE}= V_{GE}, I_C= 250 µA	3.75		5.75	V
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	V_{GE}= 15 V, I_C= 40A, Tj= 25°C V_{GE}= 15 V, I_C= 40A, Tj= 125°C		1.9 1.7	2.5	V V

(#) Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

ELECTRICAL CHARACTERISTICS (CONTINUED)

Table 7: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}(1)	Forward Transconductance	V_{CE} = 15 V, I_C= 20 A		20		S
C_{ies} C_{oes} C_{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{CE} = 25V, f = 1 MHz, V_{GE} = 0		4550 350 105		pF pF pF
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	V_{CE} = 390 V, I_C = 40 A, V_{GE} = 15V, (see Figure 20)		214 30 96		nC nC nC
I_{CL}	Turn-Off SOA Minimum Current	V_{clamp} = 480 V , Tj = 150°C R_G = 100 Ω, V_{GE}= 15V	200			A

Table 8: Switching On

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$ Eon (2)	Turn-on Delay Time Current Rise Time Turn-on Current Slope Turn-on Switching Losses	V_{CC} = 390 V, I_C = 40 A R_G= 3.3Ω, V_{GE}= 15V, Tj= 25°C (see Figure 18)		43 17 2060 330	 450	ns ns A/µs µJ
$t_{d(on)}$ t_r $(di/dt)_{on}$ Eon (2)	Turn-on Delay Time Current Rise Time Turn-on Current Slope Turn-on Switching Losses	V_{CC} = 390 V, I_C = 40 A R_G= 3.3Ω, V_{GE}= 15V, Tj= 125°C (see Figure 18)		42 19 1900 640		ns ns A/µs µJ

2) Eon is the turn-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs & DIODE are at the same temperature (25°C and 125°C)

Table 9: Switching Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$ $t_d(_{off})$ t_f E_{off} (3) E_{ts}	Off Voltage Rise Time Turn-off Delay Time Current Fall Time Turn-off Switching Loss Total Switching Loss	V_{cc} = 390 V, I_C = 40 A, R_{GE} = 3.3 Ω , V_{GE} = 15 V T_J = 25 °C (see Figure 18)		25 140 45 720 1050	 970 1420	ns ns ns µJ µJ
$t_r(V_{off})$ $t_d(_{off})$ t_f E_{off} (3) E_{ts}	Off Voltage Rise Time Turn-off Delay Time Current Fall Time Turn-off Switching Loss Total Switching Loss	V_{cc} = 390 V, I_C = 40 A, R_{GE} = 3.3 Ω , V_{GE} = 15 V Tj = 125 °C (see Figure 18)		60 170 77 1400 2040		ns ns ns µJ µJ

(3)Turn-off losses include also the tail of the collector current.

Figure 3: Output Characteristics

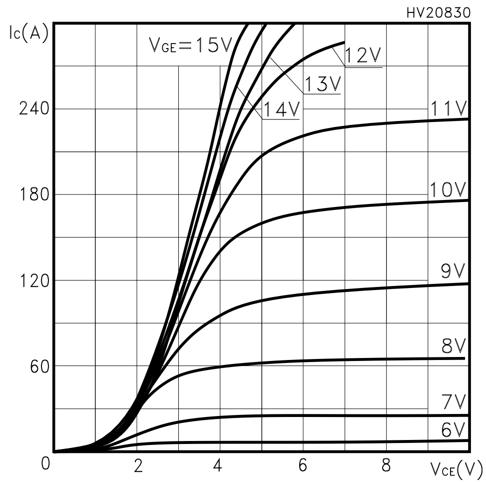


Figure 6: Transfer Characteristics

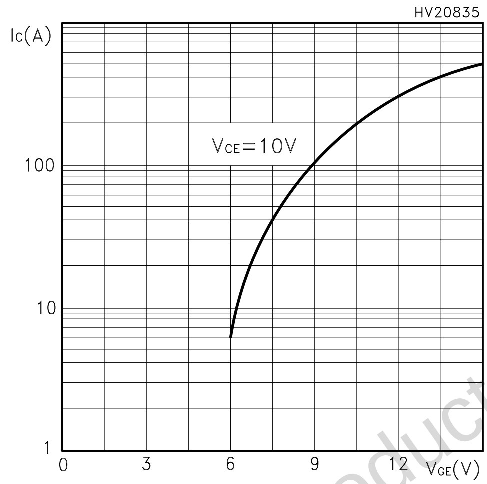


Figure 4: Transconductance

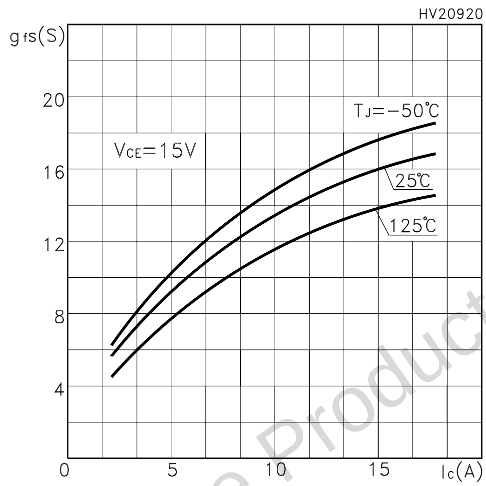


Figure 7: Collector-Emitter On Voltage vs Temperature

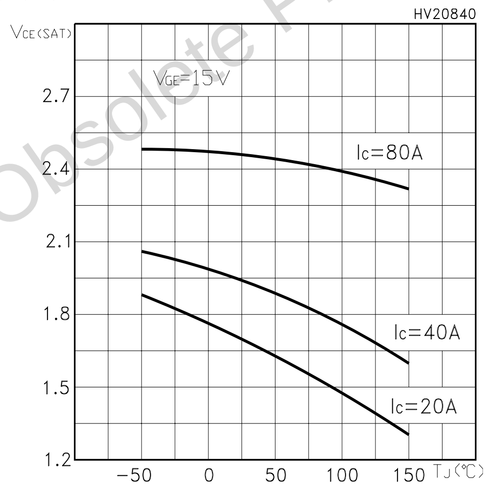


Figure 5: Collector-Emitter On Voltage vs Collector Current

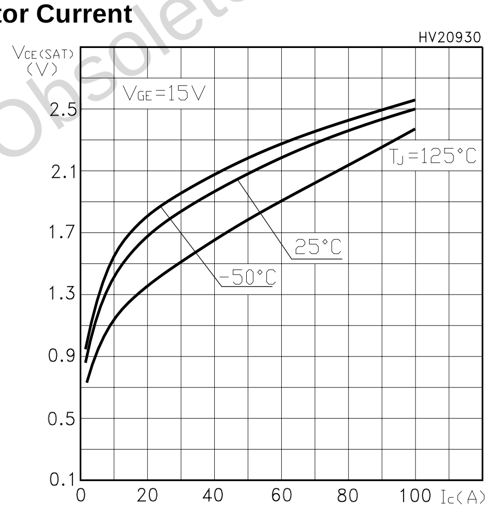


Figure 8: Normalized Gate Threshold vs Temperature

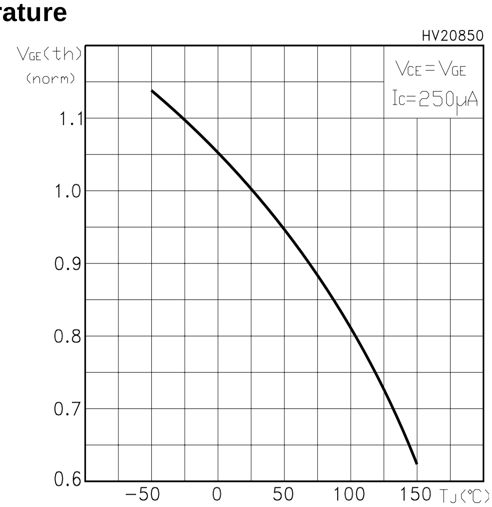


Figure 9: Normalized Breakdown Voltage vs Temperature

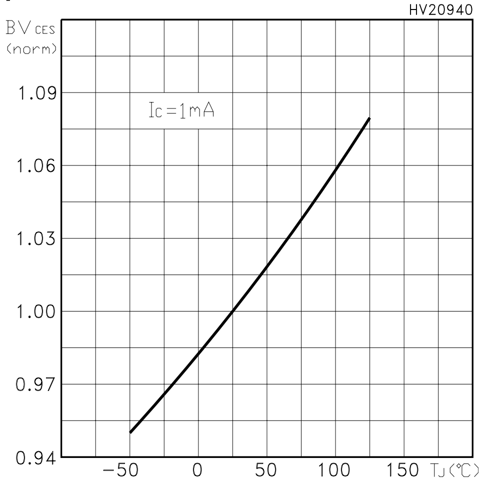


Figure 12: Gate Charge vs Gate-Emitter Voltage

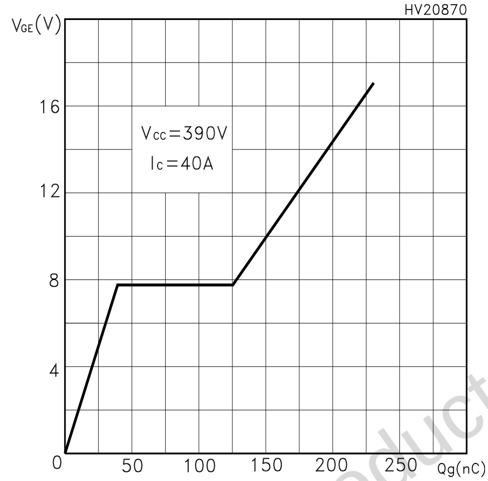


Figure 10: Capacitance Variations

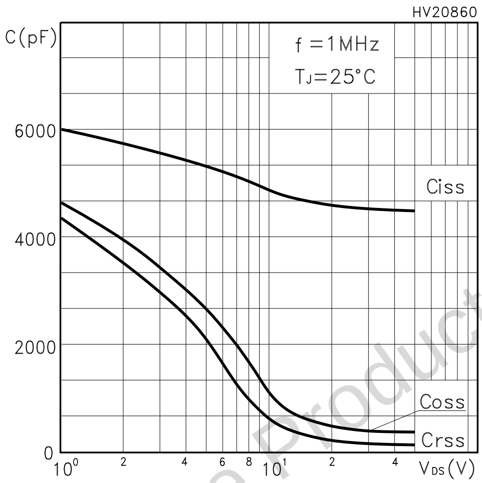


Figure 13: Total Switching Losses vs Temperature

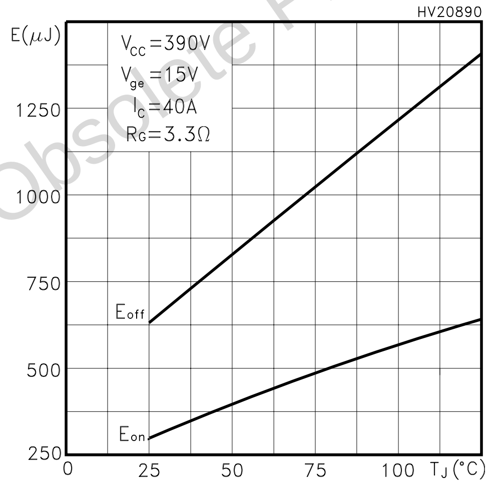


Figure 11: Total Switching Losses vs Gate Resistance

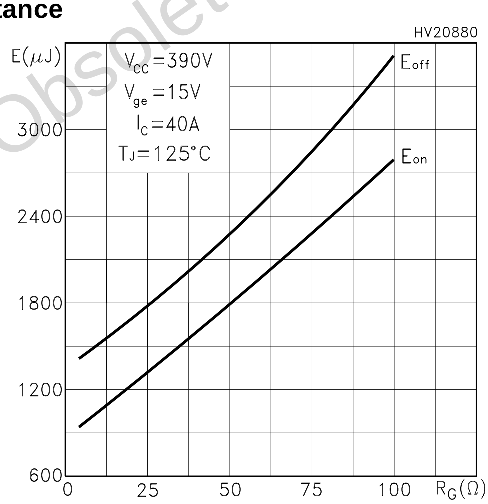


Figure 14: Total Switching Losses vs Collector Current

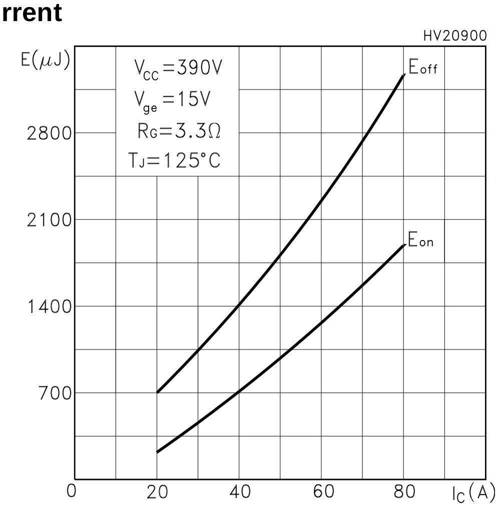


Figure 15: Thermal Impedance

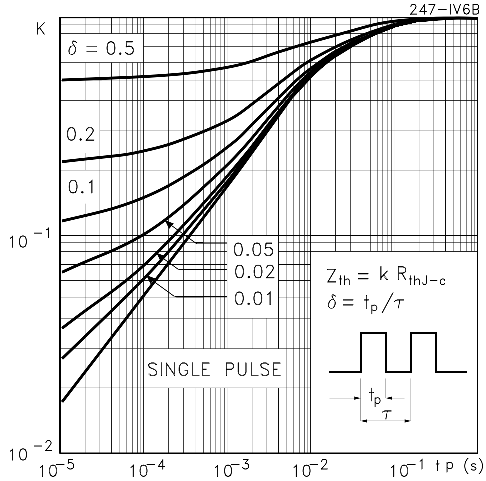


Figure 16: Turn-Off SOA

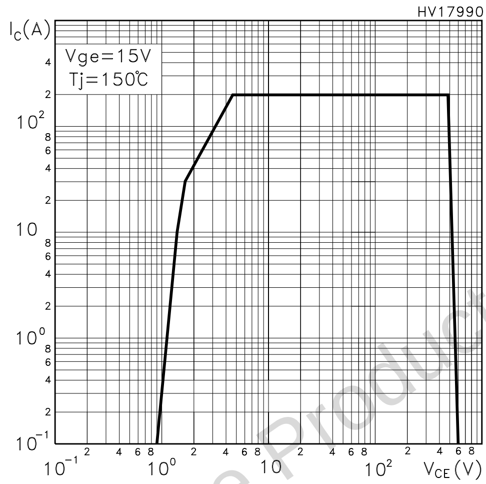
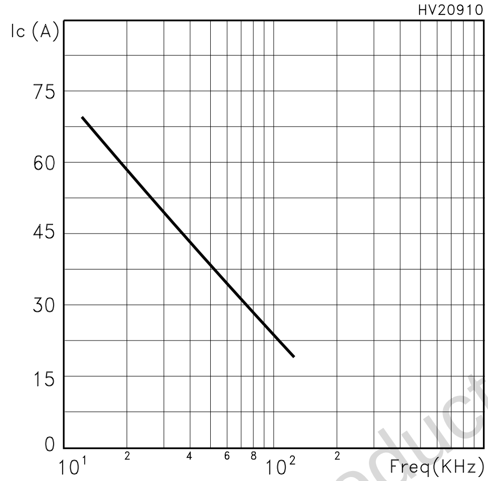


Figure 17: Ic vs Frequency



For a fast IGBT suitable for high frequency applications, the typical collector current vs. maximum operating frequency curve is reported. That frequency is defined as follows:

$$f_{MAX} = (P_D - P_C) / (E_{ON} + E_{OFF})$$

1) The maximum power dissipation is limited by maximum junction to case thermal resistance:

$$P_D = \Delta T / R_{THJ-C}$$

considering $\Delta T = T_J - T_C$ = 125 °C- 75 °C = 50°C

2) The conduction losses are:

$$P_C = I_C * V_{CE(SAT)} * \delta$$

with 50% of duty cycle, V_{CESAT} typical value @125°C.

3) Power dissipation during ON & OFF commutations is due to the switching frequency:

$$P_{SW} = (E_{ON} + E_{OFF}) * freq.$$

4) Typical values @ 125°C for switching losses are used (test conditions: V_{CE} = 390V, V_{GE} = 15V, R_G = 3.3 Ohm). Furthermore, diode recovery energy is included in the E_{ON} (see note 2), while the tail of the collector current is included in the E_{OFF} measurements (see note 3).

Figure 18: Test Circuit for Inductive Load Switching

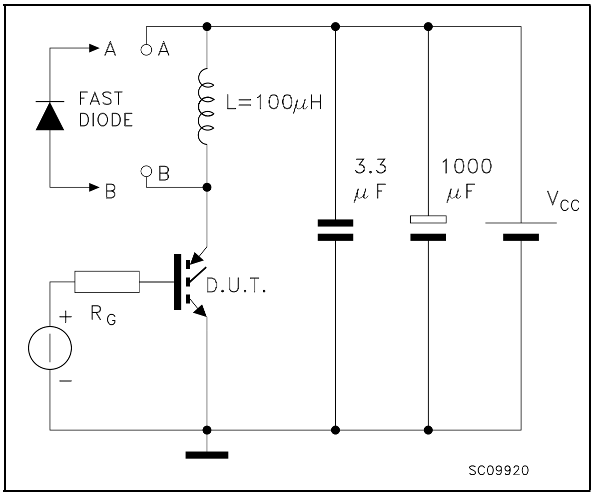


Figure 19: Switching Waveforms

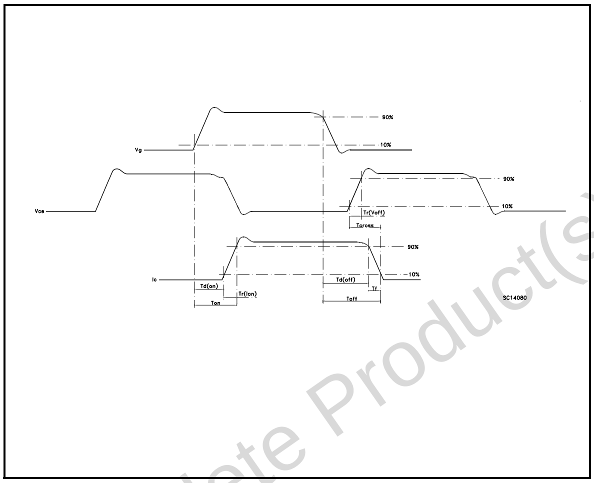
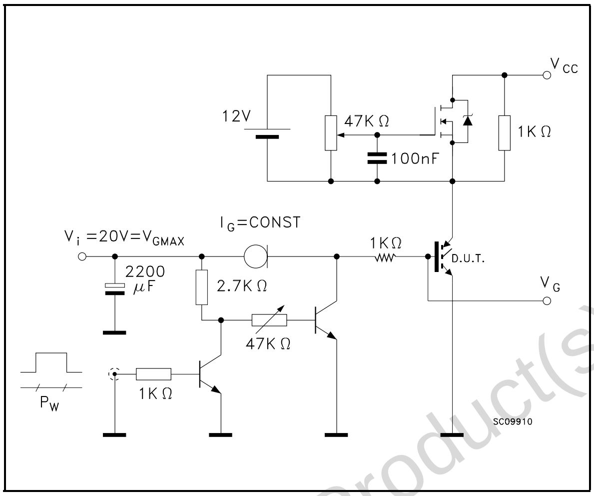


Figure 20: Gate Charge Test Circuit



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	

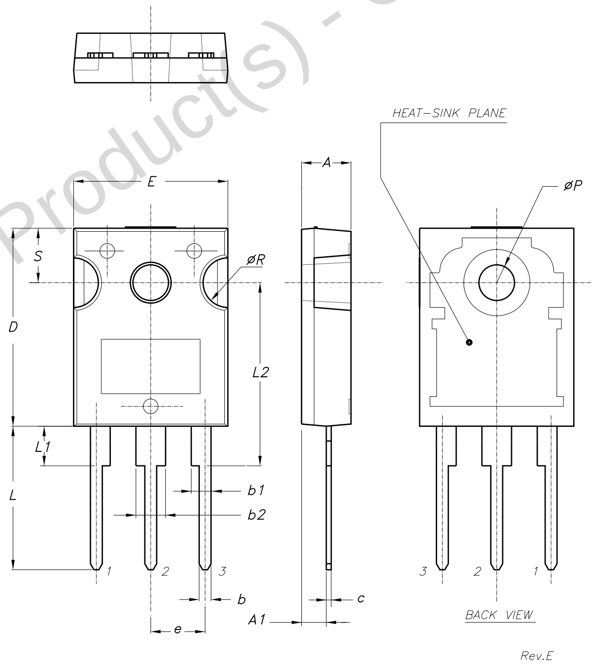


Table 10: Revision History

Date	Revision	Description of Changes
13-Jul-2004	9	Stylesheet update. No content change
14-Jul-2004	10	Some datas have been updated